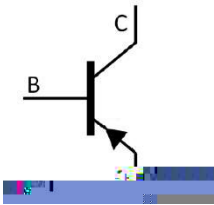


9 5 : .> // x 6 4 6 ! - } â 'ož Silicon PNP transistor in a SOT-89 Plastic Package.

ó 9 äož
High voltage.

ä 9 O ò èož
High voltage control circuit.

Ã W] Ô · / Equivalent Circuit



PIN1 y Base PIN 2

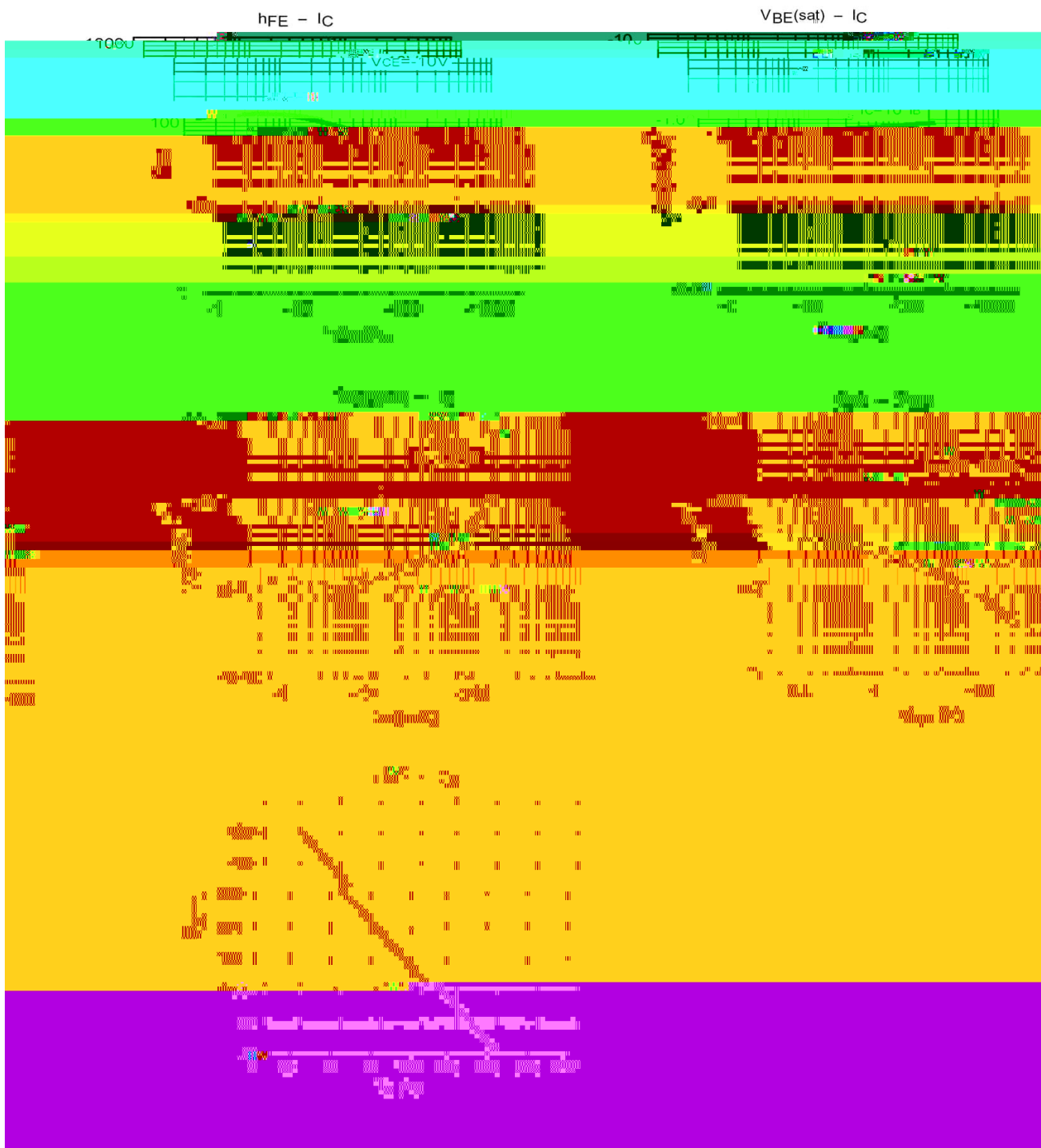
④ Absolute Maximum Ratings(Ta=25℃ ;)

@ f Parameter	Symbol	f > Rating	% y Unit
Collector to Base Voltage	V _{CBO}	-400	V
Collector to Emitter Voltage	V _{CEO}	-400	V
Emitter to Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous	I _C	-300	mA
Collector Power Dissipation	P _C	500	mW
Junction Temperature	T _j	150	
Storage Temperature Range	T _{stg}	-55 ~ 150	

④ Electrical Characteristics(Ta=25℃ ;)

@ f Parameter	Symbol	Test Conditions	Min	Typ	Max	% y Unit
Collector to Base Breakdown Voltage	V _{CBO}	I _C =-100 A I _E =0	-400			V
Collector to Emitter Breakdown Voltage	V _{CEO}	I _C =-1.0mA I _B =0	-400			V
Emitter to Base Breakdown Voltage	V _{EBO}	I _E =-100 A I _C =0	-5.0			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-300V I _E =0			-0.1	A
Emitter Cut-Off Current	I _{CES}	V _{CE} =-400V V _{BE} =0			-1	A
Emitter Base Cut-Off Current	I _{EBO}	V _{EB} =-4.0V I _C =0			-0.1	A
DC Current Gain	h _{FE(1)}	V _{CE} =-10V I _C =-10mA	80		300	
	h _{FE(2)}	V _{CE} =-10V I _C =-1.0mA	70			
	h _{FE(3)}	V _{CE} =-10V I _C =-100mA	40			
Collector to Emitter Saturation Voltage	V _{CE(sat) (1)}	I _C =-10mA I _B =-1.0mA			-0.2	V
	V _{CE(sat) (2)}	I _C =-50mA I _B =-5.0mA			-0.3	V
Emitter to Base Saturation Voltage	V _{BE(sat)}	I _C =-10mA I _B =-1.0mA			-0.75	V
Transition Frequency	f _T	V _{CE} =-5.0V I _C =-10mA f=30MHz	50			MHz

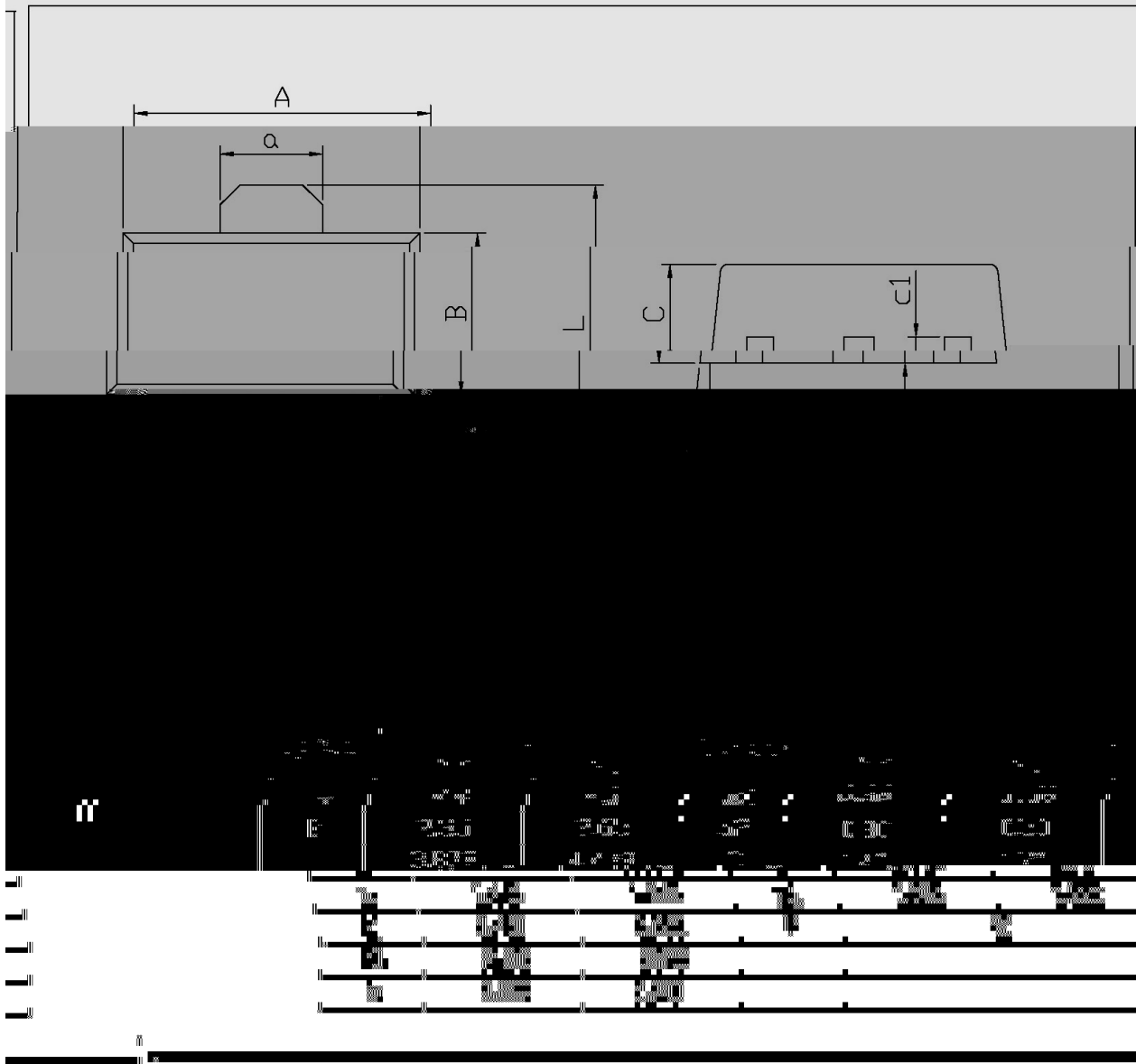
Electrical Characteristic Curve



Ø □ =) ⌀ / Package Dimensions

ST1-89

单位: mm



MMBTA94T
Rev.F Apr.-2019

šWD t...•Žč (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6



^ačy

- 10• Ä ½ “† 150 ½180 - k ž • 60 ½90sec;
- 20• Q > “† 245 r5 - k ž • 4 Ò 5 r0.5sec;
- 30•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

- 1.Preheating:150~180 - , Time:60~90sec.
- 2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.
3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »]